

a portion of a first selected one of said stacked metal layers and a portion of a second selected one of said stacked metal layers, said second selected stacked metal layer portion above and adjacent said first selected stacked metal layer portion;

a first capacitor dielectric layer over said first selected stacked metal layer portion;

a first capacitor metal plate layer over said first capacitor dielectric layer;

A4  
COND.  
a second capacitor dielectric layer under said second selected stacked metal layer portion;

a second capacitor metal plate layer under said second capacitor dielectric layer and over and extending from said first capacitor metal plate layer; and

a metal capacitor via layer between and connecting said first capacitor metal plate layer and said second capacitor metal plate layer, said metal capacitor via layer forming a first terminal of said capacitor structure; and

a first via connecting said first selected stacked metal layer portion and said second selected stacked metal layer portion to form a second terminal of said capacitor structure.

✓  
Cancel claims 9-14 directed to the non-elected method.

IN THE ABSTRACT:

AS  
Page 14, line 1, change the title to read - Structure to Increase Density of MIM Capacitors Between Adjacent Metal Layers in an Integrated Circuit -

REMARKS

Claims 1-8 remain in the application with claim 1 amended to improve form. Non-elected method claims 9-14 are canceled without prejudice to the filing of a divisional application.

Reconsideration is respectfully requested for claims 1-8 as amended.